

NTB5411N, NTP5411N

Power MOSFET 80 Amps, 60 Volts N-Channel D²PAK, TO-220

Features

- Low $R_{DS(on)}$
- High Current Capability
- Avalanche Energy Specified
- These are Pb-Free Devices

Applications

- LED Lighting and LED Backlight Drivers
- DC-DC Converters
- DC Motor Drivers
- Power Supplies Secondary Side Synchronous Rectification

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ Unless otherwise specified)

| Parameter | | | Symbol | Value | Unit |
|---|------------------------|---------------------------|----------------|------------|------------------|
| Drain-to-Source Voltage | | | V_{DSS} | 60 | V |
| Gate-to-Source Voltage – Continuous | | | V_{GS} | ± 20 | V |
| Gate-to-Source Voltage – Nonrepetitive ($T_P < 10 \mu\text{s}$) | | | V_{GS} | ± 30 | V |
| Continuous Drain Current $R_{\theta JC}$ (Note 1) | Steady State | $T_C = 25^\circ\text{C}$ | I_D | 80 | A |
| | | $T_C = 100^\circ\text{C}$ | | 61 | |
| Power Dissipation $R_{\theta JC}$ (Note 1) | Steady State | $T_C = 25^\circ\text{C}$ | P_D | 166 | W |
| Pulsed Drain Current | $t_p = 10 \mu\text{s}$ | | I_{DM} | 185 | A |
| Operating and Storage Temperature Range | | | T_J, T_{stg} | -55 to 175 | $^\circ\text{C}$ |
| Source Current (Body Diode) | | | I_S | 75 | A |
| Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 50 V_{dc}, V_{GS} = 10 V_{dc}, I_{L(pk)} = 75 \text{ A}, L = 0.1 \text{ mH}, R_G = 25 \Omega$) | | | E_{AS} | 280 | mJ |
| Lead Temperature for Soldering Purposes, 1/8" from Case for 10 Seconds | | | T_L | 260 | $^\circ\text{C}$ |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Max | Unit |
|--|-----------------|-----|---------------------------|
| Junction-to-Case (Drain) Steady State (Note 1) | $R_{\theta JC}$ | 0.9 | $^\circ\text{C}/\text{W}$ |
| | $R_{\theta JA}$ | 43 | |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [1 oz] including traces).

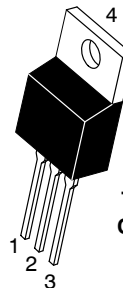
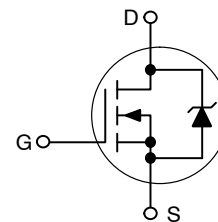


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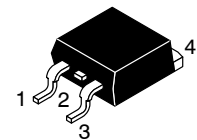
<http://onsemi.com>

| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | $I_D \text{ MAX}$ (Note 1) |
|---------------|--------------------------|----------------------------|
| 60 V | 10 m Ω @ 10 V | 80 A |

N-Channel

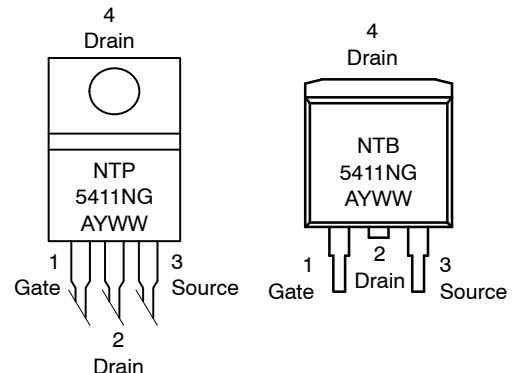


TO-220AB
CASE 221A
STYLE 5



D²PAK
CASE 418B
STYLE 2

MARKING DIAGRAM & PIN ASSIGNMENT



G = Pb-Free Device
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTB5411N, NTP5411N

ELECTRICAL CHARACTERISTICS (T_J = 25°C Unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|--------------------------------------|---|------------------------|------|------|-------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-to-Source Breakdown Voltage | V _{(BR)DSS} | V _{DS} = 0 V, I _D = 250 μA | 60 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V _{(BR)DSS} /T _J | | | 54.2 | | mV/°C |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V V _{DS} = 60 V | T _J = 25°C | | 10 | μA |
| | | | T _J = 150°C | | 100 | |
| Gate-Body Leakage Current | I _{GSS} | V _{DS} = 0 V, V _{GS} = ±20 V | | | ±100 | nA |

ON CHARACTERISTICS (Note 2)

| | | | | | | |
|--|-------------------------------------|---|-----|------|------|-------|
| Gate Threshold Voltage | V _{GS(th)} | V _{GS} = V _{DS} , I _D = 250 μA | 2.0 | 3.2 | 4.0 | V |
| Negative Threshold Temperature Coefficient | V _{GS(th)} /T _J | | | 6.6 | | mV/°C |
| Drain-to-Source On Voltage | V _{DS(on)} | V _{GS} = 10 V, I _D = 80 A | | 0.71 | 0.92 | V |
| | | V _{GS} = 10 V, I _D = 40 A, 150°C | | 0.65 | | |
| Static Drain-to-Source On-Resistance | R _{DS(on)} | V _{GS} = 10 V, I _D = 40 A | | 8.4 | 10 | mΩ |
| Forward Transconductance | g _{FS} | V _{GS} = 15 V, I _D = 40 A | | 70 | | S |

CHARGES, CAPACITANCES & GATE RESISTANCE

| | | | | | | |
|-----------------------|---------------------|--|--|------|------|----|
| Input Capacitance | C _{iss} | V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz | | 3365 | 4500 | pF |
| Output Capacitance | C _{oss} | | | 615 | | |
| Transfer Capacitance | C _{rss} | | | 230 | | |
| Total Gate Charge | Q _{G(TOT)} | V _{GS} = 10 V, V _{DS} = 48 V, I _D = 80 A | | 92 | 130 | nC |
| Threshold Gate Charge | Q _{G(TH)} | | | 4.1 | | |
| Gate-to-Source Charge | Q _{GS} | | | 19 | | |
| Gate-to-Drain Charge | Q _{GD} | | | 43 | | |

SWITCHING CHARACTERISTICS, V_{GS} = 10 V (Note 3)

| | | | | | | |
|---------------------|---------------------|--|--|-----|--|----|
| Turn-On Delay Time | t _{d(on)} | V _{GS} = 10 V, V _{DD} = 48 V, I _D = 80 A, R _G = 9.1 Ω | | 22 | | ns |
| Rise Time | t _r | | | 122 | | |
| Turn-Off Delay Time | t _{d(off)} | | | 116 | | |
| Fall Time | t _f | | | 113 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|--------------------------------|-----------------|---|------------------------|------|------|-----|-----------------|
| Forward Diode Voltage | V _{SD} | V _{GS} = 0 V I _S = 37.5 A | T _J = 25°C | | 0.91 | 1.1 | V _{dc} |
| | | | T _J = 150°C | | 0.8 | | |
| Reverse Recovery Time | t _{rr} | I _S = 37.5 A _{dc} , V _{GS} = 0 V _{dc} , di _S /dt = 100 A/μs | | 62 | | ns | |
| Charge Time | t _a | | | 43 | | | |
| Discharge Time | t _b | | | 19 | | | |
| Reverse Recovery Stored Charge | Q _{RR} | | | 0.15 | | | μC |

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

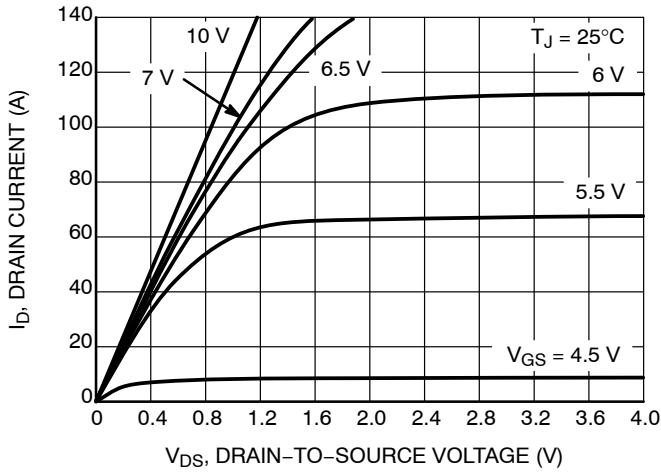


Figure 1. On-Region Characteristics

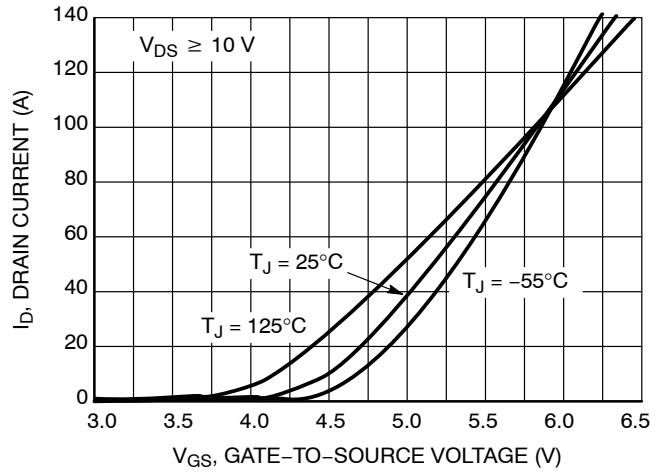


Figure 2. Transfer Characteristics

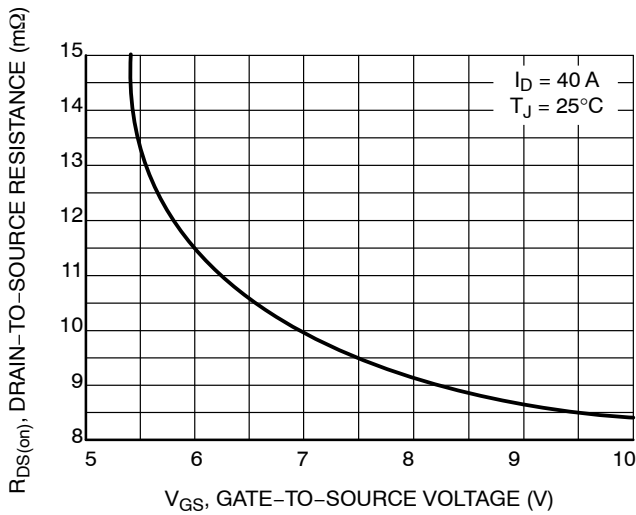


Figure 3. On-Resistance vs. Gate-to-Source Voltage

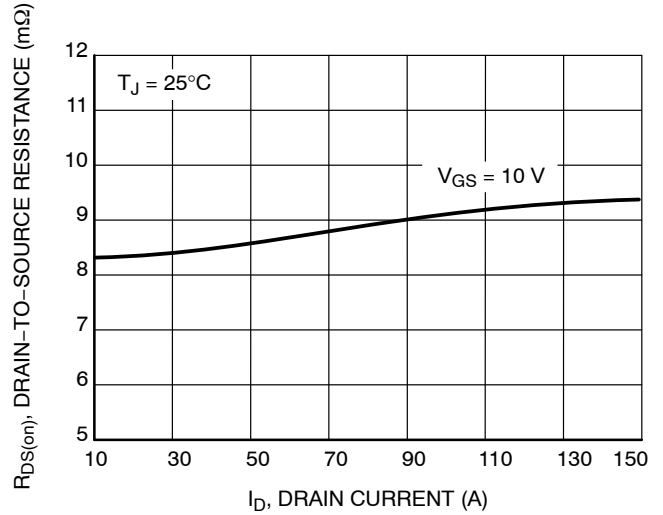


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

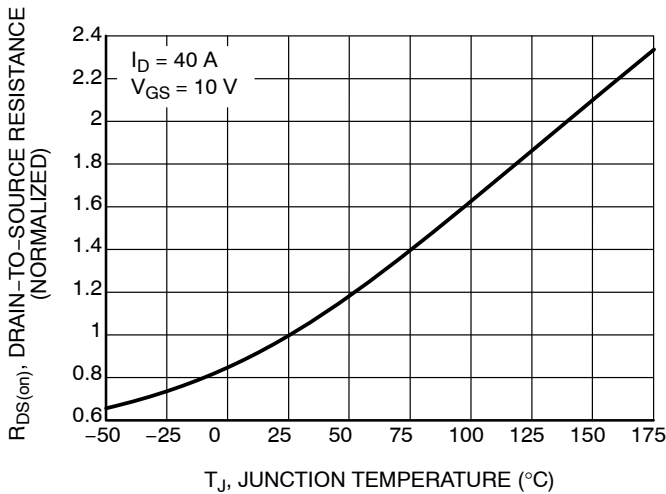


Figure 5. On-Resistance Variation with Temperature

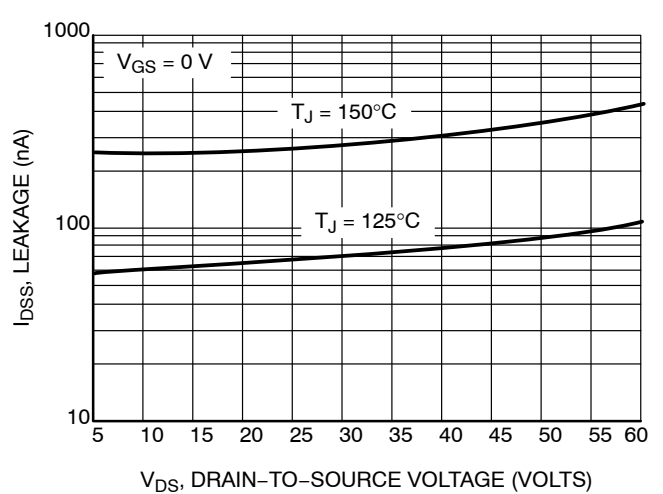


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTB5411N, NTP5411N

TYPICAL PERFORMANCE CURVES

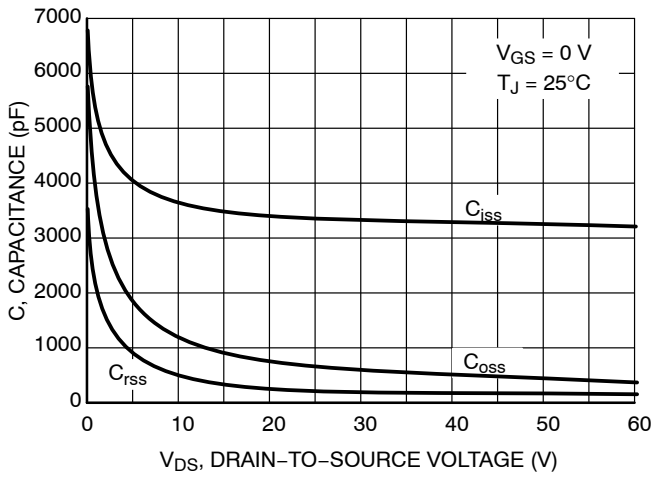


Figure 7. Capacitance Variation

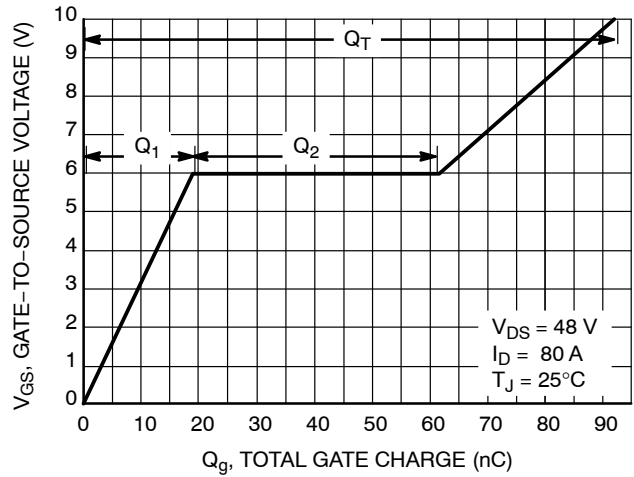


Figure 8. Gate-to-Source Voltage vs. Total Charge

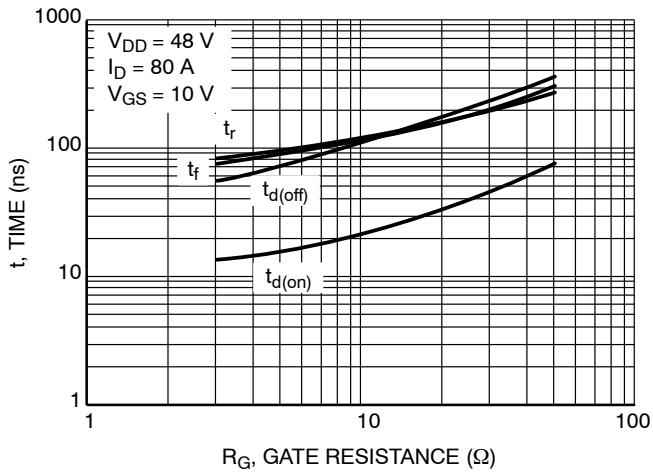


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

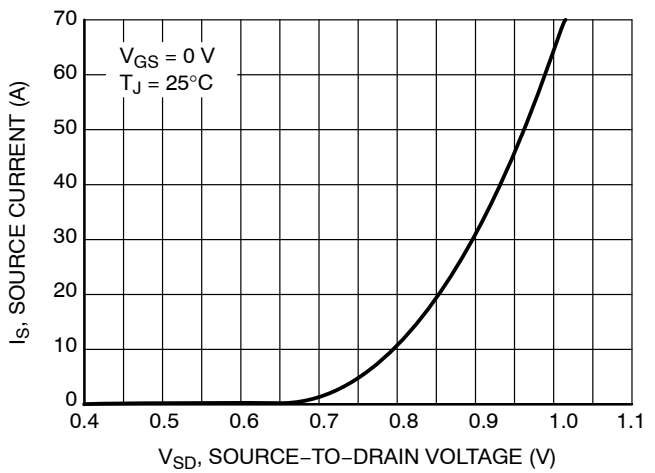


Figure 10. Diode Forward Voltage vs. Current

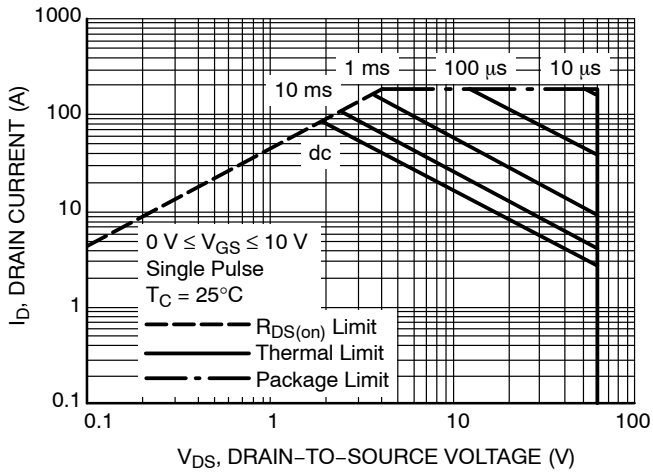


Figure 11. Maximum Rated Forward Biased Safe Operating Area

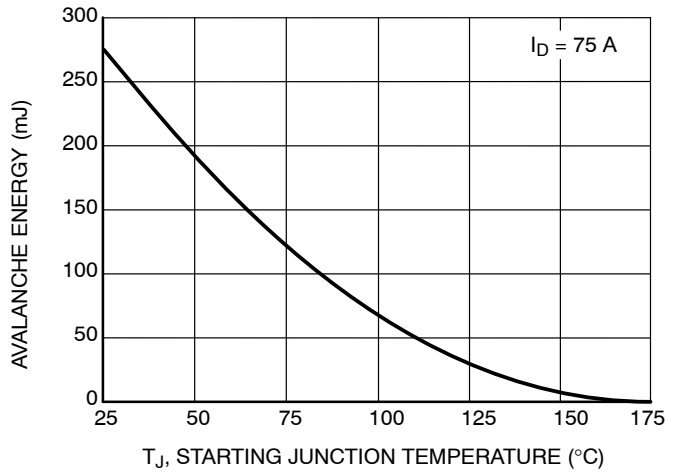


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

NTB5411N, NTP5411N

TYPICAL PERFORMANCE CURVES

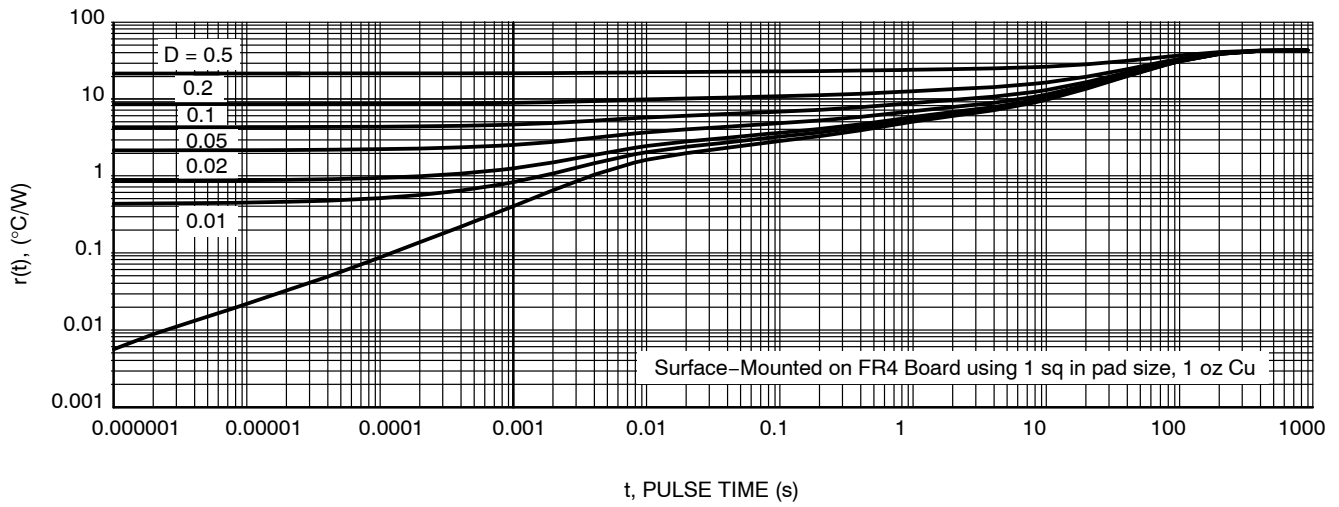


Figure 13. Thermal Response

ORDERING INFORMATION

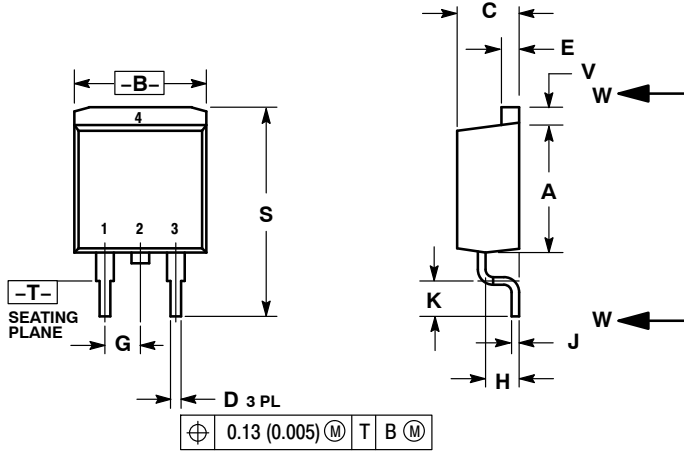
| Device | Package | Shipping [†] |
|-------------|---------------------------------|-----------------------|
| NTP5411NG | TO-220AB (Pb-Free) | 50 Units / Rail |
| NTB5411NT4G | D ² PAK (Pb-Free) | 800 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTB5411N, NTP5411N

PACKAGE DIMENSIONS

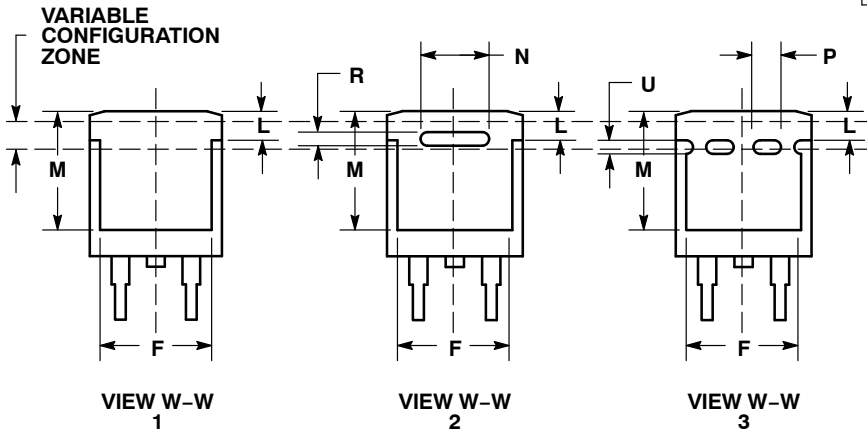
D²PAK 3
CASE 418B-04
ISSUE K



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

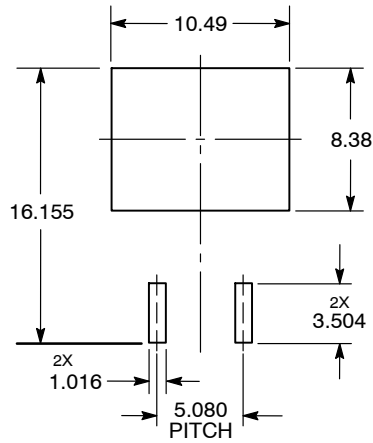
| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.340 | 0.380 | 8.64 | 9.65 |
| B | 0.380 | 0.405 | 9.65 | 10.29 |
| C | 0.160 | 0.190 | 4.06 | 4.83 |
| D | 0.020 | 0.035 | 0.51 | 0.89 |
| E | 0.045 | 0.055 | 1.14 | 1.40 |
| F | 0.310 | 0.350 | 7.87 | 8.89 |
| G | 0.100 BSC | | 2.54 BSC | |
| H | 0.080 | 0.110 | 2.03 | 2.79 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.090 | 0.110 | 2.29 | 2.79 |
| L | 0.052 | 0.072 | 1.32 | 1.83 |
| M | 0.280 | 0.320 | 7.11 | 8.13 |
| N | 0.197 REF | | 5.00 REF | |
| P | 0.079 REF | | 2.00 REF | |
| R | 0.039 REF | | 0.99 REF | |
| S | 0.575 | 0.625 | 14.60 | 15.88 |
| V | 0.045 | 0.055 | 1.14 | 1.40 |



STYLE 2:

- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



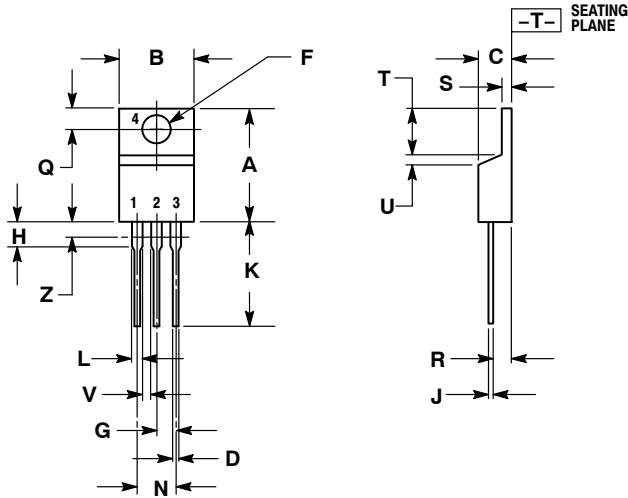
DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NTB5411N, NTP5411N

PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AF



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.405 | 9.66 | 10.28 |
| C | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.161 | 3.61 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.014 | 0.025 | 0.36 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

STYLE 5:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

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